

In re Patent Application of:  
GRANT  
Serial No. 10/781,977  
Filing Date: FEBRUARY 19, 2004

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In the Claims:

This listing of claims replaces all prior versions and listing of claims in the application.

Claims 1-16 (Cancelled).

17. (Currently amended) A semiconductor image sensor comprising:

at least one pixel comprising a photosensing portion and a silicide formation prevention coating thereon, said silicide formation prevention coating having a thickness to operate as an anti-reflective surface at a desired wavelength range so that the coating performs dual functions.

18. (Currently amended) A semiconductor image sensor according to Claim 17, wherein the silicide formation prevention coating has a maximum transmission at a wavelength range of substantially blue light ~~one of the dual functions of the coating comprises a fabrication function.~~

19. (Currently amended) A semiconductor image sensor according to Claim ~~[[18]]~~ 17, wherein the silicide formation prevention coating has a maximum transmission at a wavelength range of substantially 450nm ~~fabrication function comprises the coating preventing silicide formation on the photosensing portion.~~

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20. (Currently amended) A semiconductor image sensor according to Claim 17, wherein the silicide formation prevention coating comprises a layer of silicon nitride and a layer of silicon dioxide adjacent thereto ~~one of the dual functions of the coating comprises an in-use function.~~

21. (Currently amended) A semiconductor image sensor according to Claim 20, wherein the layer of silicon nitride is substantially 300Å thick and the layer of silicon dioxide is substantially 250Å thick ~~in-use function comprises the coating functioning as an anti-reflective surface.~~

22. (Currently amended) A semiconductor image sensor according to Claim 17, wherein the photosensing [[part]] portion comprises a photo-diode.

23. (Previously presented) A semiconductor image sensor according to Claim 22, wherein the photo-diode comprises a pinned photo-diode.

24. (Previously presented) A semiconductor image sensor according to Claim 22, wherein the photo-diode comprises a partially pinned photo-diode.

Claims 25-28 (Canceled).

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29. (Currently amended) A method for making a semiconductor image sensor comprising:

forming at least one pixel having a photosensing portion; and

forming a silicide formation prevention coating on the photosensing portion, the silicide formation prevention coating having a thickness to operate as an anti-reflective surface at a desired wavelength range so that the coating performs [[a]] dual function functions.

30. (Currently amended) A method according to Claim 29, wherein the silicide formation prevention coating has a maximum transmission at a wavelength range of substantially blue light ~~one of the dual functions of the coating comprises a fabrication function.~~

31. (Currently amended) A method according to Claim [[30]] 29, wherein the silicide formation prevention coating has a maximum transmission at a wavelength range of substantially 450nm ~~fabrication function comprises the coating preventing silicide formation on the photosensing portion.~~

32. (Currently amended) A method according to Claim 29, wherein the silicide formation prevention coating comprises a layer of silicon nitride and a layer of silicon dioxide

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~~adjacent thereto one of the dual functions of the coating  
comprises an in use function.~~

33. (Currently amended) A method according to Claim 32, wherein the layer of silicon nitride is substantially 300Å thick and the layer of silicon dioxide is substantially 250Å thick ~~in use function comprises the coating functioning as an anti-reflective surface.~~

34. (Currently amended) A method according to Claim 29, wherein forming the silicide formation prevention coating comprises a self-aligning technique.

35. (Currently amended) A method according to Claim [[30]] 29, wherein the photosensing portion comprises a photo-diode.

36. A method according to Claim 35, wherein the photo-diode comprises a pinned photo-diode.

37. A method according to claim 35, wherein the photo-diode comprises a partially pinned photo-diode.